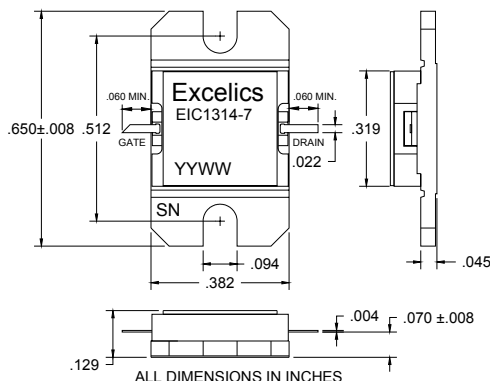


ISSUED 11/13/2008

### 13.75-14.50 GHz 7-Watt Internally Matched Power FET

#### FEATURES

- 13.75– 14.50GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +38.5 dBm Output Power at 1dB Compression
- 6.0 dB Power Gain at 1dB Compression
- 25% Power Added Efficiency
- Hermetic Metal Flange Package
- 100% Tested for DC, RF, and  $R_{TH}$



#### ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )



Caution! ESD sensitive device.

SYMBOL	PARAMETERS/TEST CONDITIONS <sup>1</sup>	MIN	TYP	MAX	UNITS
$P_{1dB}$	Output Power at 1dB Compression $f = 13.75\text{-}14.50\text{GHz}$ $V_{DS} = 10\text{ V}$ , $I_{DSQ} \approx 2400\text{mA}$	38	38.5		dBm
$G_{1dB}$	Gain at 1dB Compression $f = 13.75\text{-}14.50\text{GHz}$ $V_{DS} = 10\text{ V}$ , $I_{DSQ} \approx 2400\text{mA}$	5	6		dB
$\Delta G$	Gain Flatness $f = 13.75\text{-}14.50\text{GHz}$ $V_{DS} = 10\text{ V}$ , $I_{DSQ} \approx 2400\text{mA}$			$\pm 0.6$	dB
IMD3	Output 3rd Order Intermodulation Distortion $\Delta f = 10\text{ MHz}$ 2-Tone Test; $P_{out} = 28.0\text{ dBm S.C.L.}^2$ $V_{DS} = 10\text{ V}$ , $I_{DSQ} \approx 65\% IDSS$ $f = 14.50\text{ GHz}$	-41	-45		dBc
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}$ , $I_{DSQ} \approx 2400\text{mA}$ $f = 13.75\text{-}14.50\text{GHz}$		25		%
$I_{d1dB}$	Drain Current at 1dB Compression $f = 13.75\text{-}14.50\text{GHz}$		2400	3000	mA
$I_{DSS}$	Saturated Drain Current $V_{DS} = 3\text{ V}$ , $V_{GS} = 0\text{ V}$		4	6.5	A
$V_P$	Pinch-off Voltage $V_{DS} = 3\text{ V}$ , $I_{DS} = 38\text{ mA}$		-2.5	-4.0	V
$R_{TH}$	Thermal Resistance <sup>3</sup>		2.6	3	$^\circ\text{C/W}$

Note: 1) Tested with 50 Ohm gate resistor.

2) S.C.L. = Single Carrier Level.

3) Overall  $R_{th}$  depends on case mounting.

#### MAXIMUM RATING AT $25^\circ\text{C}^{1,2}$

SYMBOLS	PARAMETERS	ABSOLUTE <sup>1</sup>	CONTINUOUS <sup>2</sup>
$V_{ds}$	Drain-Source Voltage	15	10V
$V_{gs}$	Gate-Source Voltage	-5	-4V
$P_{in}$	Input Power	35dBm	@ 3dB Compression
$T_{ch}$	Channel Temperature	175 $^\circ\text{C}$	175 $^\circ\text{C}$
$T_{stg}$	Storage Temperature	-65 to +175 $^\circ\text{C}$	-65 to +175 $^\circ\text{C}$
$P_t$	Total Power Dissipation	50W	50W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085

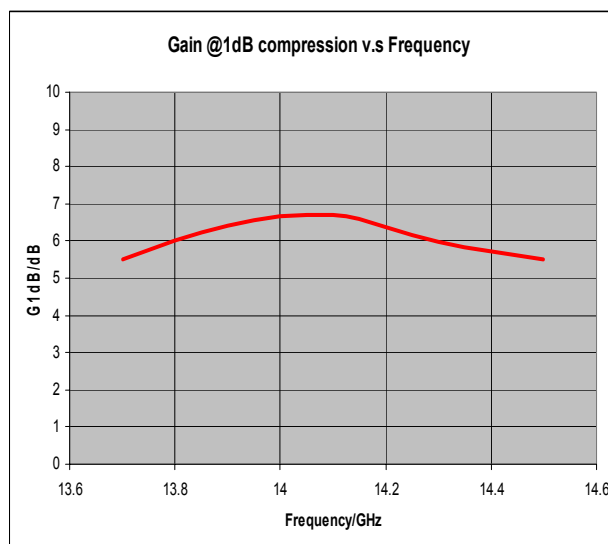
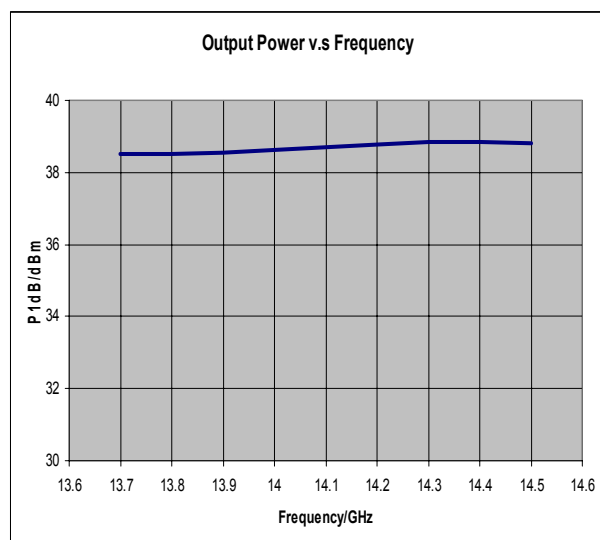
Phone: 408-737-1711 Fax: 408-737-1868 Web: [www.excelics.com](http://www.excelics.com)

page 1 of 4

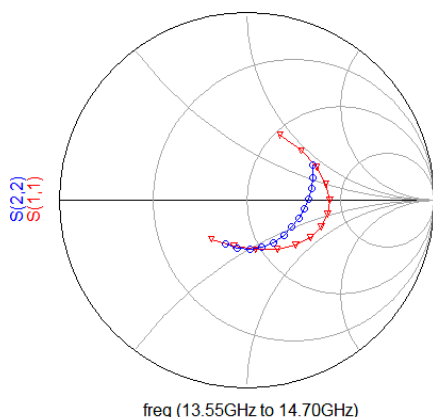
issued November 2008

ISSUED 11/13/2008

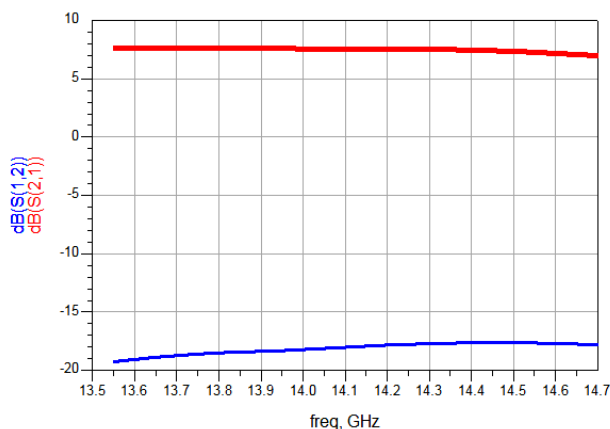
## 13.75-14.50 GHz 7-Watt Internally Matched Power FET



**P1dB v.s Frequency**



**G1dB v.s Frequency**



freq	S			
	S(1,1)	S(1,2)	S(2,1)	S(2,2)
13.55GHz	0.390 / 62.905	0.109 / 166.430	2.399 / -166.775	0.400 / 28.140
13.65GHz	0.394 / 42.462	0.113 / 156.639	2.416 / -176.970	0.374 / 19.250
13.74GHz	0.412 / 25.322	0.117 / 147.027	2.413 / 173.203	0.350 / 10.434
13.84GHz	0.431 / 11.600	0.120 / 137.742	2.406 / 163.800	0.328 / 1.246
13.93GHz	0.442 / 0.277	0.121 / 128.880	2.403 / 154.760	0.309 / -8.397
14.03GHz	0.439 / -9.628	0.124 / 120.530	2.390 / 145.879	0.292 / -18.935
14.13GHz	0.423 / -19.253	0.126 / 111.480	2.387 / 136.912	0.280 / -30.613
14.22GHz	0.394 / -29.810	0.129 / 102.401	2.383 / 127.686	0.272 / -43.473
14.32GHz	0.353 / -42.015	0.130 / 93.312	2.377 / 118.420	0.266 / -57.638
14.41GHz	0.307 / -58.124	0.131 / 84.041	2.357 / 108.906	0.259 / -71.985
14.51GHz	0.266 / -79.873	0.132 / 74.619	2.334 / 99.207	0.258 / -86.613
14.60GHz	0.253 / -105.927	0.131 / 65.190	2.285 / 89.402	0.259 / -101.462
14.70GHz	0.281 / -132.760	0.129 / 55.990	2.223 / 79.560	0.257 / -115.760

Typical S-Parameters (T= 25°C, 50Ω system, de-embedded to edge of package)

**V<sub>DS</sub> = 10 V, I<sub>DSQ</sub> = 2400mA**

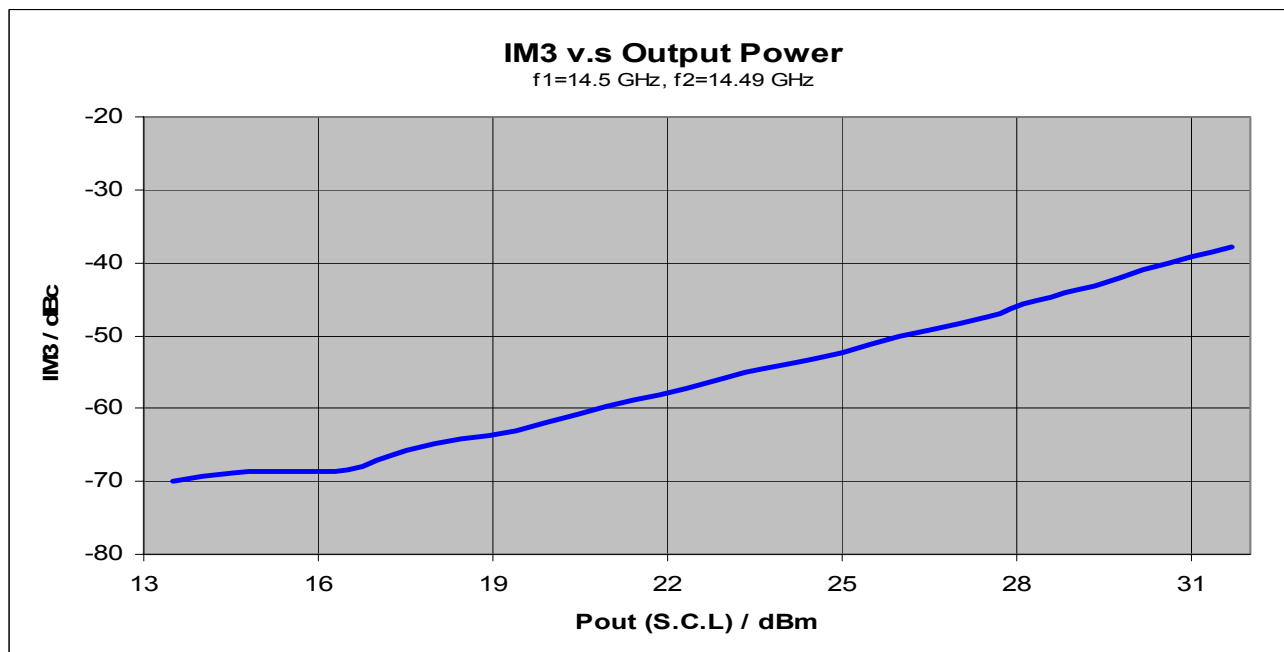
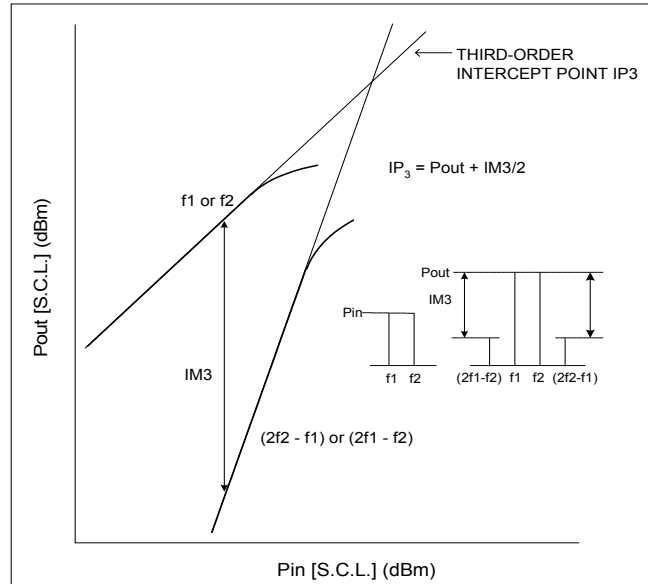
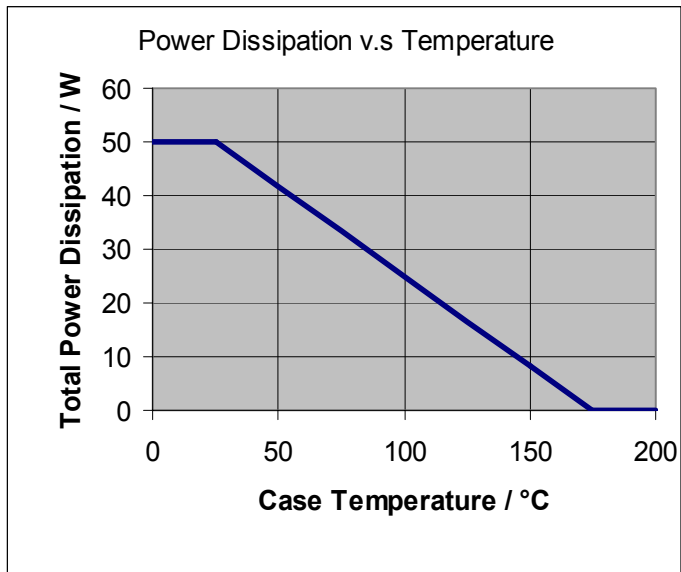
Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085

Phone: 408-737-1711 Fax: 408-737-1868 Web: [www.excelics.com](http://www.excelics.com)

page 2 of 4

issued November 2008



Typical IMD3 Data (T= 25°C)

$V_{DS} = 10$  V,  $I_{DSQ} \approx 65\%$   $ID_{SS}$

ISSUED 11/13/2008

## 13.75-14.50 GHz 7-Watt Internally Matched Power FET

### DISCLAIMER

EXCELICS SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. EXCELICS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN.

### LIFE SUPPORT POLICY

EXCELICS SEMICONDUCTOR PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF EXCELICS SEMICONDUCTOR, INC.

AS HERE IN:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

---

Specifications are subject to change without notice.

Excelics Semiconductor, Inc. 310 De Guigne Drive, Sunnyvale, CA 94085

Phone: 408-737-1711 Fax: 408-737-1868 Web: [www.excelics.com](http://www.excelics.com)

page 4 of 4

issued November 2008